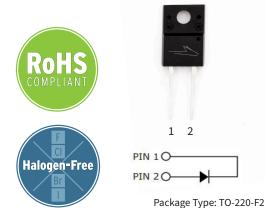


### 3rd Generation 600 V, 3 A Silicon Carbide Schottky Diode

### **Description**

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



either the Cree name and/or logo or the Wolfspeed name and/or logo.

Marking: C3D03060
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#### **Features**

- Optimized for PFC Boost Diode Application
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior
- Fully Isolated Case
- Extremely Fast Switching

#### **Applications**

- Switch Mode Power Supplies (SMPS)
- Free Wheeling Diodes in Inverter Stages
- Boost for PFC & DC-DC Stages
- Solar Inverters
- AC/DC Converters

# **Maximum Ratings** (T<sub>c</sub> = 25°C Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Notes	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	600	V			
DC Blocking Voltage	V <sub>DC</sub>	600	V			
		8		T <sub>c</sub> = 25 °C	E' . 2	
Continuous Forward Current	I <sub>F</sub>	3		T <sub>c</sub> = 125 °C	Fig. 3	
		2		T <sub>c</sub> = 150 °C		
Repetitive Peak Forward Surge Current		11		$T_c = 25  ^{\circ}\text{C}, t_p = 10  \text{ms},  \text{Half Sine Wave}$		
	FRM	6	А	$T_c = 110 ^{\circ}\text{C}$ , $t_p = 10 \text{ms}$ , Half Sine Wave		
Non-Repetitive Forward Surge Current	I <sub>FSM</sub>	18		$T_c = 25  ^{\circ}\text{C},  t_p = 10  \text{ms},  \text{Half Sine Wave}$	Fig. 8	
		14.5		$T_c = 110  ^{\circ}\text{C,t}_p = 10  \text{ms, Half Sine Wave}$		
Non-Repetitive Peak Forward	l F,Max	100		$T_c = 25 ^{\circ}\text{C}, t_p = 10 \mu\text{s}, \text{Pulse}$	Fig 8.	
Surge Current		80		$T_{c} = 110^{\circ}\text{C}, t_{p} = 10 \mu\text{s}, \text{Pulse}$		
Power Dissipation	P <sub>tot</sub>	27.3	W	T <sub>c</sub> = 25 °C	Fig. 4	
		11.8		T <sub>c</sub> = 110 °C		
Diode dV/dt Ruggedness	dV/dt	200	V/ns	V <sub>R</sub> = 0-600V		
22. 1. (2. 1. )	ʃi²dt	1.6	A <sup>2</sup> s	$T_c = 25  ^{\circ}\text{C}, t_p = 10 \text{ms}$		
i <sup>2</sup> t value (Per Leg)		1.0		$T_c = 110 ^{\circ}\text{C}, t_p = 10 \text{ms}$		

### **Electrical Characteristics**

Parameter	Symbol	Тур.	Max.	Unit	Test Conditions	Notes
5 177		1.5	1.7	.,	I <sub>F</sub> = 3 A, T <sub>j</sub> = 25 °C	F:- 1
Forward Voltage	V <sub>F</sub>	1.8	2.4	V	I <sub>F</sub> = 3 A, T <sub>j</sub> = 175 °C	Fig. 1
Reverse Current		4	20	μА	$V_R = 600 \text{ V}, T_j = 25 \text{ °C}$	Fig. 2
	I <sub>R</sub>	8	80		$V_R = 600 \text{ V}, T_j = 175 \text{ °C}$	
Total Capacitive Charge	Q <sub>c</sub>	7.6		nC	$V_R = 400 \text{ V}, T_j = 25 \text{ °C}, I_F = 3 \text{ A}$	Fig. 5
		166			$V_R = 0 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	
Total Capacitance	c	14		pF	$V_R = 200 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	Fig. 6
		11			$V_R = 400 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	
Capacitance Stored Energy	E <sub>c</sub>	1.1		μJ	V <sub>R</sub> = 400 V	Fig. 7

#### Notes:

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

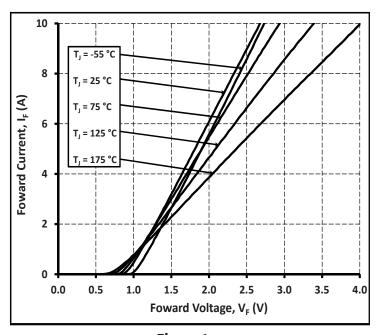
### **Thermal & Mechanical Characteristics**

Parameter	Symbol	Value	Unit	Notes
Thermal Resistance, Junction to Case (Typical)	R <sub>0, JC (TYP)</sub>	5.5	°C/W	
Junction Temperature	T <sub>j</sub>	-55 to +175	۰٫	
Case & Storage Temperature	T <sub>c</sub>	-55 to +175	°C	
TO 220 Mounting Torque	-	1	Nm	M3 Screw
TO-220 Mounting Torque		8.8	lbf-in	6-32 Screw

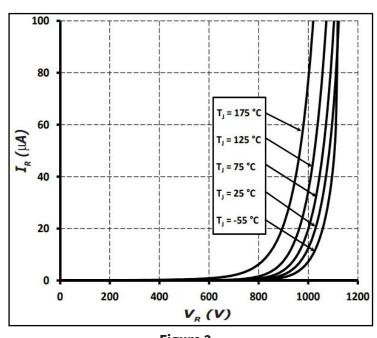
## **Electrostatic Discharge (ESD) Classifications**

Parameter	Symbol	Notes
Human Body Model	НВМ	Class 3B (≥ 8000 V)
Charge Device Model	CDM	Class C3 (≥ 1000 V)

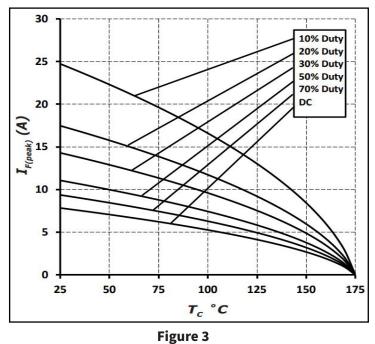
### **Typical Performance**



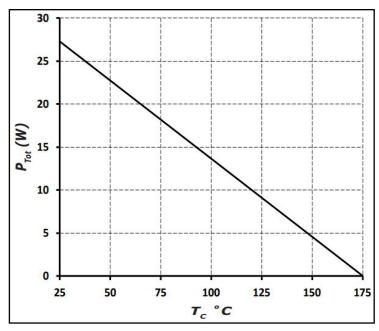
**Figure 1**Forward Characteristics



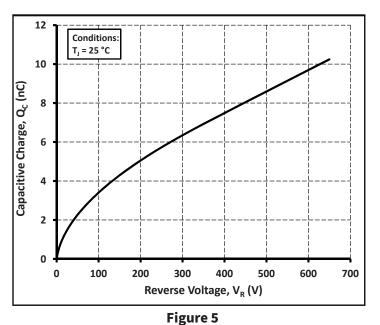
**Figure 2**Reverse Characteristics



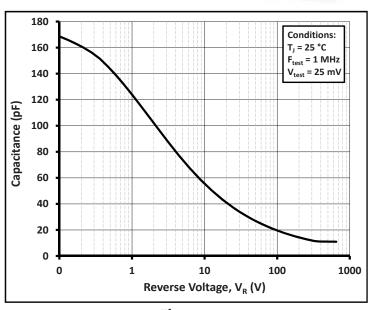
Current Derating



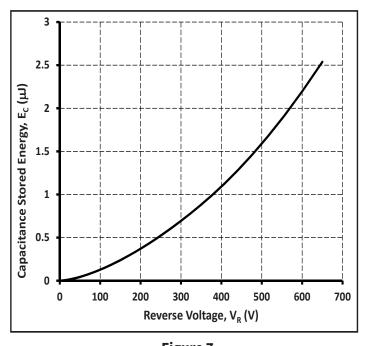
**Figure 4**Power Derating



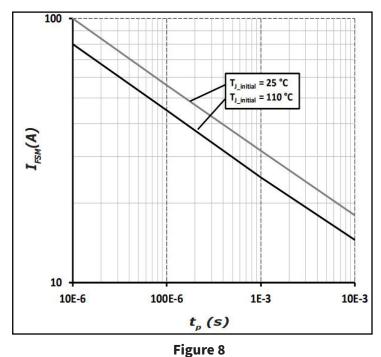
Total Capacitance vs. Reverse Voltage



**Figure 6**Capacitace vs. Reverse Voltage



**Figure 7**Capacitance Stored Energy



Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)

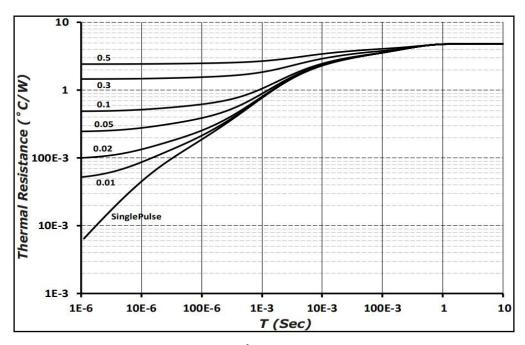
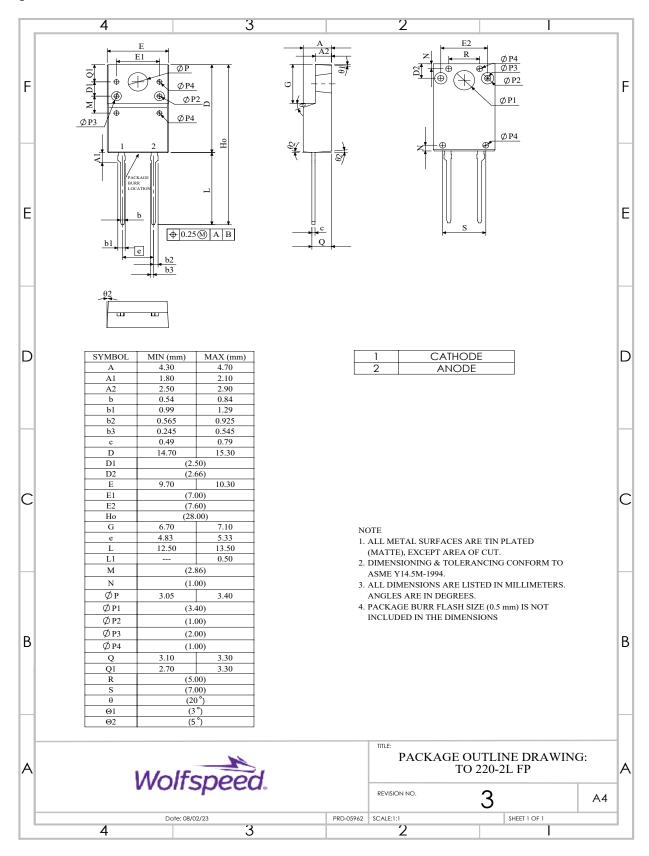


Figure 9 Transient Thermal Impedance

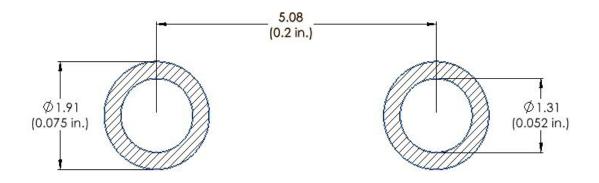
### **Package Dimensions & Pin-Out**

Package: TO-220-F2



### **Recommended Solder Pad Layout**

Primary dimensions shown in mm.



# **Product Ordering Information**

Order Number	Packing Type
C3D03060F	Tube

# **Revision History**

Document Version	Date of Release	Description of Changes
F	February- 2019	Initial Release
7	October-2023	Update Package Drawing Update Landing Pad Updated Branding Updated Package Image
8	November-2023	Correct POD A1, b1, and Q

### Notes & Disclaimer

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